



Form 149 (Modified)

**Information Disclosure
Statement By Applicant**

(Use Several Sheets if Necessary)

Atty Docket No.
NOVLP096/NVLS-2902

Application No.:
10/815,560

Applicant:
Wongsenakhum et al.

Filing Date
March 31, 2004

Group
2823

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	A1	6,635,965	10.21.03	Lee et al.	—	—	
	A2	6,607,976	08/19/03	Chen et al.	—	—	
	A3	6,740,585	05/25/04	Yoon et al.	—	—	
	A4	6,861,356	03/01/05	Matsuse et al.	—	—	
	A5	6,107,200 A	08.2000	Takagi et al.	—	—	
	A6	6,844,258	01.18.05	Fair et al.	—	—	
	A7	6,174,812	01/16/01	Hsiung, et al.	—	—	
	A8	6,566,250	05/20/03	Tu, et al.	—	—	
	A9	6,566,262	05/20/03	Rissman, et al.	—	—	
	A10	6,706,625	03/16/04	Sudijono, et al.	—	—	
	A11	2004/0044127	03.04.04	Okubo et al.	—	—	
	A12	2004/0206267	10.21.04	Sambasivan et al.	—	—	

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation
							Yes No
	B1	WO01/27147	04/19/01	WIPO			X

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	C1	U.S. Office Action mailed July 17, 2002, from U.S. Application No. 09/975,074 [Atty Dkt. NOVLP033/NVLS-000498].
	C2	U.S. Office Action mailed February 8, 2005, from U.S. Application No. 10/649,351 [Atty Dkt. NOVLP033X1/NVLS-000498X1].
	C3	U.S. Office Action mailed July 14, 2005, from U.S. Application No. 10/649,351 [Atty Dkt. NOVLP033X1/NVLS-000498X1].
	C4	Presentation by Inventor James Fair: "Chemical Vapor Deposition of Refractory Metal Silicides," 27 Pages, 1983
	C5	Saito et al., "A Novel Copper Interconnection Technology Using Self Aligned Metal Capping Method," IEEE, 3 Pages, 2001
	C6	U.S. Office Action mailed June 22, 2004, from U.S. Application No. 10/435,010 [Atty Dkt. NOVLP058/NVLS-000730].
	C7	U.S. Office Action mailed March 23, 2005, from U.S. Application No. 10/690,492 [Atty Dkt. NOVLP063/NVLS-000615].

Examiner Initial	Date Considered
<i>Michelle Gottada</i>	12/14/05

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified)	Atty Docket No. NOVLP096/NVLS-2902	Application No.: 10/815,560
Information Disclosure Statement By Applicant	Applicant: Wongsenakhum et al.	
(Use Several Sheets if Necessary)	Filing Date March 31, 2004	Group 2823

Other Documents

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

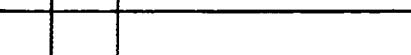


Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No. NOVLP096/NVLS-2902	Application No.: 10/815,560
	Applicant: Wongsenakhum et al.	
	Filing Date March 31, 2004	Group 2823

U.S. Patent Documents

Foreign Patent or Published Foreign Patent Application

Other Documents

Other Documents		
Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	C1	U.S. Office Action mailed November 8, 2004, from U.S. Application No. 10/984,126 [Atty Dkt. NOVLP058D1/NVLS-000732D1].
	C2	Chan et al., "Methods for Growing Low-Resistivity Tungsten Film", Novellus Systems, Inc., filed November 1, 2005, Application No. 11/265,531, pages 1-35. [NOVLP137/NVLS-0003093]
Examiner 	Date Considered 12/22/05	

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.